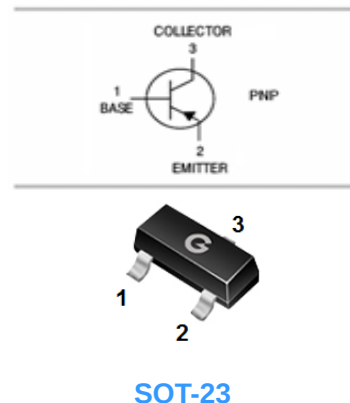


Features

- Epitaxial planar die construction
- Complimentary to MMBTA42
- Ultra-small surface mount package

HF



Mechanical Data

- Case: SOT-23
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMBTA92	SOT-23	3000 pcs / Tape & Reel	2D

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	-300	V
Collector-Emitter Breakdown Voltage	V _{CEO}	-300	V
Emitter-Base Breakdown Voltage	V _{EBO}	-5	V
Continuous Collector Current	I _C	-0.5	A

Thermal Characteristics

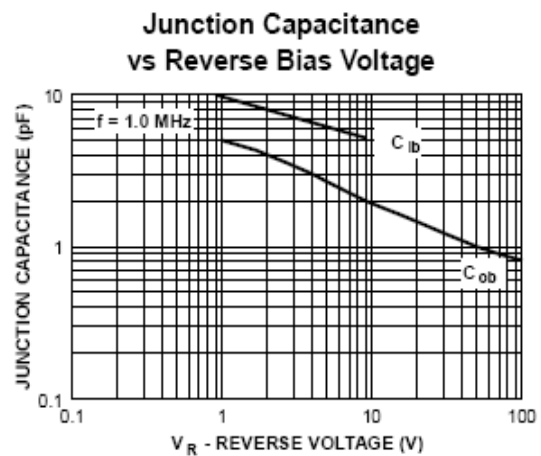
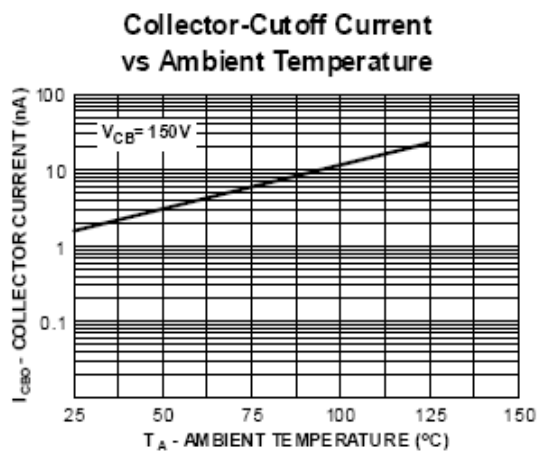
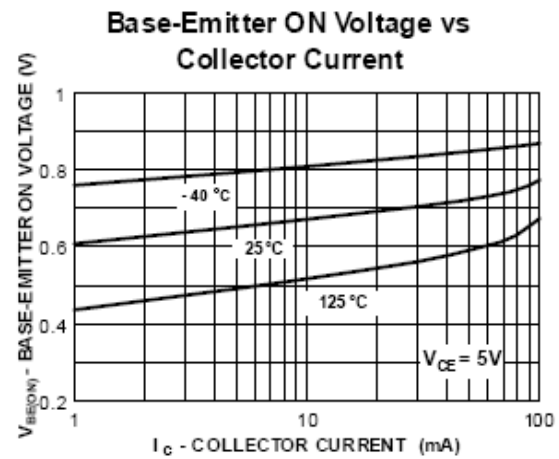
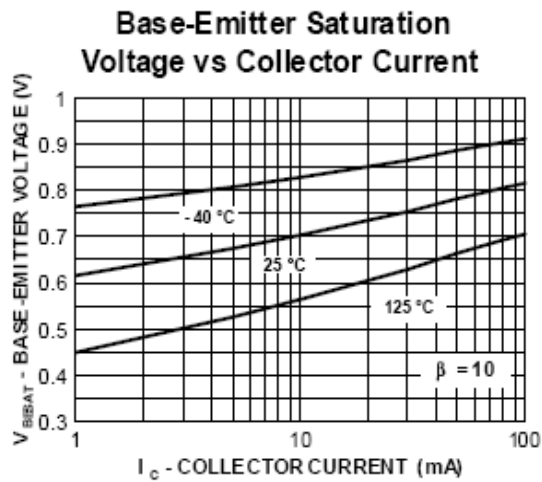
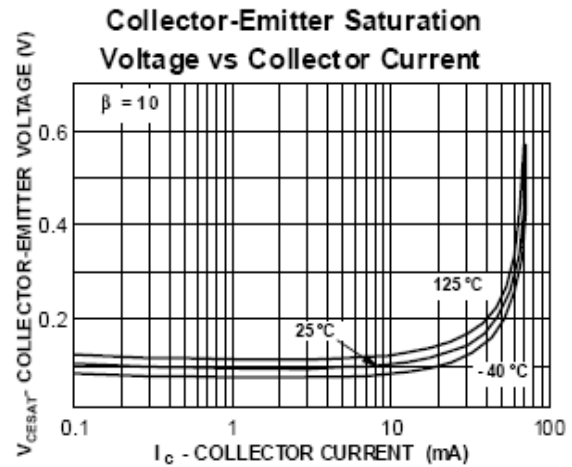
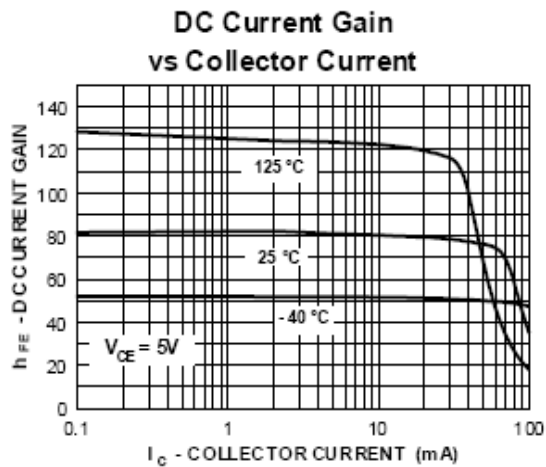
Parameter	Symbol	Value	Unit
Power Dissipation	P _D	300	mW
Thermal Resistance (Junction-to-Ambient) ^{*1}	R _{θJA}	335	°C/W
Thermal Resistance (Junction-to-Case) ^{*1}	R _{θJC}	162	°C/W
Thermal Resistance (Junction-to-Lead) ^{*1}	R _{θJL}	126	°C/W
Operating junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

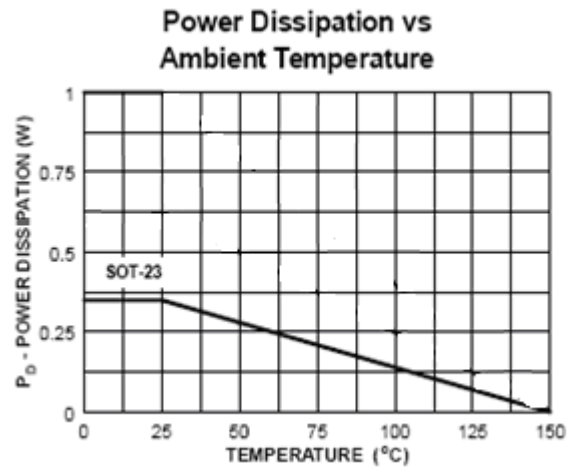
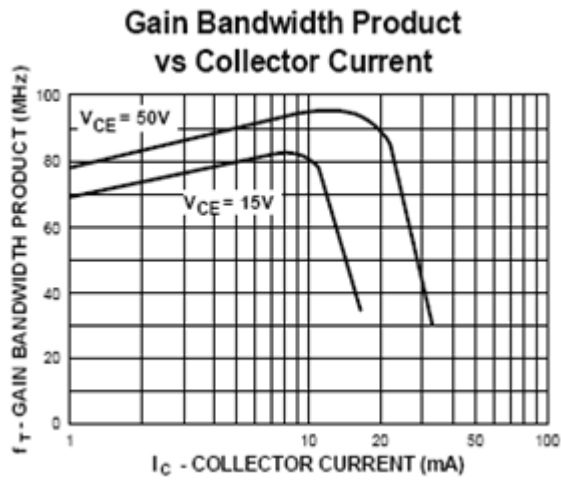
Note 1: The data tested by surface mounted on a 15mm * 15mm * 1mm FR4-epoxy P.C.B

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

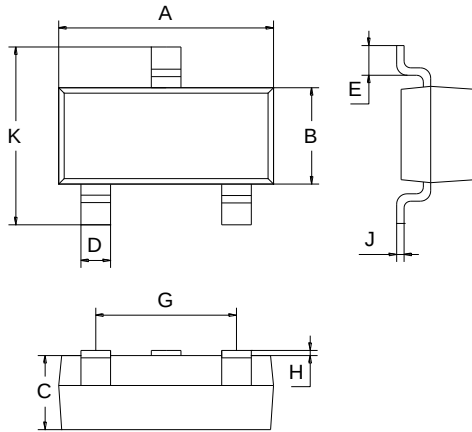
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-300	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-300	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -200\text{V}, I_E = 0$	-	-	-250	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$	-	-	-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	25	-	-	-
		$V_{CE} = -10\text{V}, I_C = -10\text{mA}$	40	-	-	-
		$V_{CE} = -10\text{V}, I_C = -30\text{mA}$	25	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -20\text{mA}, I_B = -2\text{mA}$	-	-	-0.5	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -20\text{mA}, I_B = -2\text{mA}$	-	-	-0.9	V
Transition Frequency	f_T	$I_C = -10\text{mA}, V_{CE} = -20\text{V}$	50	-	-	MHz
Collector Output Capacitance	C_{OBO}	$V_{CB} = -20\text{V}, I_E = 0, f = 1\text{MHz}$	-	-	6	pF

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)





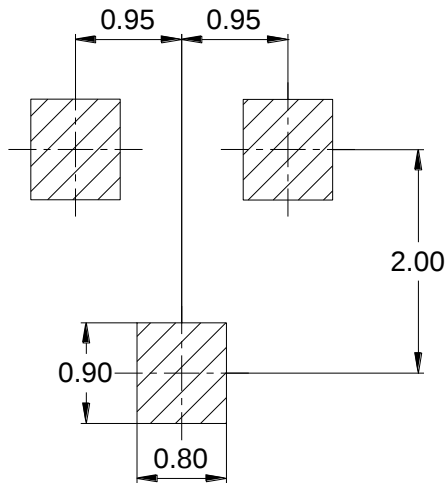
Package Outline Dimensions (Unit: mm)



SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.9	1.1
D	0.3	0.5
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.05	0.15
K	2.20	2.60

Package Outline Dimensions (Unit: mm)

SOT-23



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